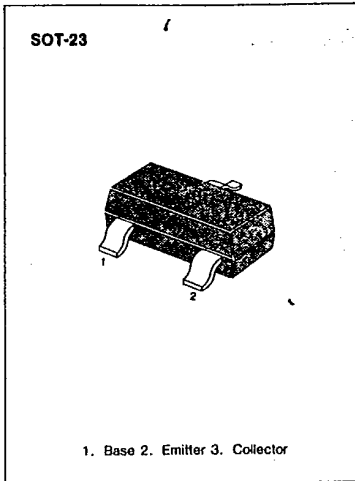


**MMBC1622D6 NPN EPITAXIAL SILICON TRANSISTOR**

**AMPLIFIER TRANSISTOR**

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)**

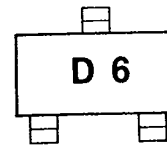
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	40	V
Collector-Emitter Voltage	V <sub>CE0</sub>	35	V
Emitter-Base Voltage	V <sub>EB0</sub>	5.0	V
Collector Current	I <sub>C</sub>	100	mA
Collector Dissipation	P <sub>C</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 25V, I <sub>E</sub> = 0		50	nA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0		50	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 0.1mA	150		
		V <sub>CE</sub> = 3V, I <sub>C</sub> = 0.5mA	200	400	
Collector-Emitter Saturation Voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA		0.3	V
Base-Emitter On Voltage	V <sub>BE (on)</sub>	I <sub>C</sub> = 0.5mA, V <sub>CE</sub> = 3V	0.55	0.65	V
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 6V, I <sub>E</sub> = 1.0mA f = 100MHz	100		MHz

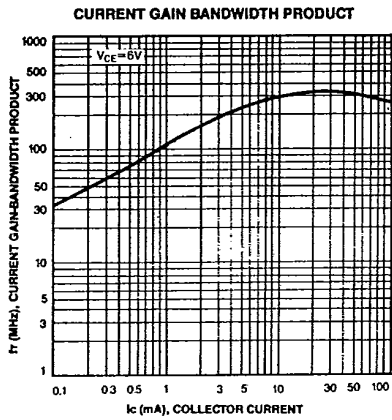
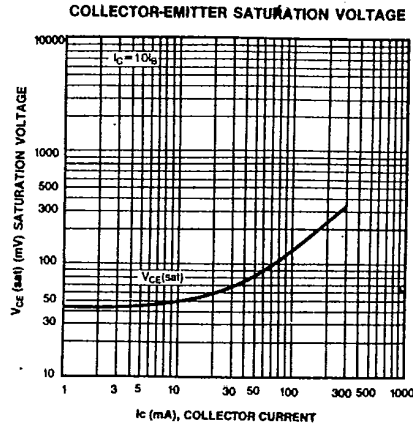
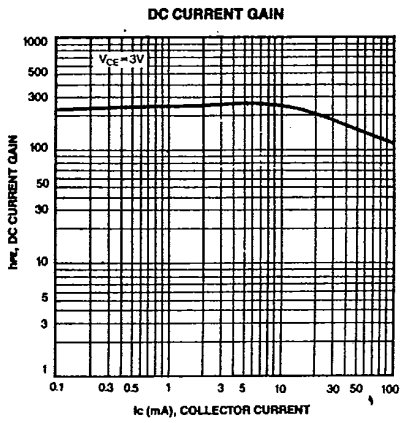
**Marking**



MMBC1622D6

NPN EPITAXIAL SILICON TRANSISTOR

T-29-19



3

